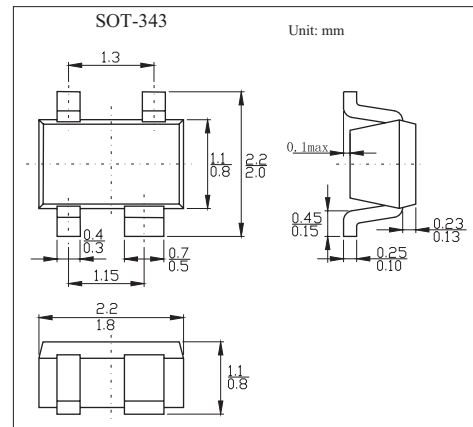


Silicon Switching Diode Array

BAS28W

■ Features

- For high-speed switching applications
- Electrical insulated diodes

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	75	V
Peak reverse voltage	V_{RM}	85	V
Forward current	I_F	200	mA
Surge forward current, $t = 1 \mu\text{s}$	I_{FS}	4.5	A
Total power dissipation, $T_s = 103^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to + 150	$^\circ\text{C}$
Junction - ambient ¹⁾	$R_{th JA}$	≤ 460	K/W
Junction - soldering point	$R_{th JS}$	≤ 190	K/W

Note

1. Package mounted on epoxy pcb $40\text{mm} \times 40\text{mm} \times 1.5\text{mm}$ / 0.5cm^2 Cu

BAS28W■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Breakdown voltage	$I_{(BR)}$	$V_R = 40\text{ V}$	85			V
Forward voltage	I_F	$I_F = 1\text{ mA}$			715	mV
		$I_F = 10\text{ mA}$			855	
		$I_F = 50\text{ mA}$			1000	
		$I_F = 150\text{ mA}$			1250	
Reverse current	I_R	$V_R = 75\text{ V}$			1	$\mu\text{ A}$
		$V_R = 25\text{ V}, T_A = 150^\circ\text{C}$			30	
		$V_R = 75\text{ V}, T_A = 150^\circ\text{C}$			50	
Diode capacitance	C_D	$f = 1\text{ MHz}; V_R = 0$			2	pF
Reverse recovery time	t_{rr}	$I_F = 10\text{ mA}, I_R = 10\text{ mA}, R_L = 100\ \Omega$ measured at $I_R = 1\text{ mA}$			6	ns

■ Marking

Marking	JTs
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